

N-Channel 60-V (D-S) MOSFET

| PRODUCT SUMMARY | | | |
|------------------------|---------------------------|------------------------|--------------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) ^a | Q_g (Typ.) |
| 60 | 0.076 at $V_{GS} = 10$ V | 4.5 | 10 nC |
| | 0.085 at $V_{GS} = 4.5$ V | 3.5 | |

FEATURES

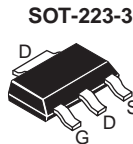
- Halogen-free
- TrenchFET[®] Power MOSFET



RoHS
COMPLIANT

APPLICATIONS

- Load Switches for Portable Devices



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted | | | | |
|---|----------------|---------------|---------------------|---|
| Parameter | Symbol | Limit | Unit | |
| Drain-Source Voltage | V_{DS} | 60 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current ($T_J = 150$ °C) | I_D | $T_C = 25$ °C | 4.5 | A |
| | | $T_C = 70$ °C | 3.2 ^a | |
| | | $T_A = 25$ °C | 2.7 | |
| | | $T_A = 70$ °C | 2.3 | |
| Pulsed Drain Current | I_{DM} | 20 | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25$ °C | 3.2 | |
| | | $T_A = 25$ °C | 2.1 ^{b, c} | |
| Maximum Power Dissipation | P_D | $T_C = 25$ °C | 4.0 | W |
| | | $T_C = 70$ °C | 3.0 | |
| | | $T_A = 25$ °C | 2.5 ^{b, c} | |
| | | $T_A = 70$ °C | 1.6 ^{b, c} | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C | |
| Soldering Recommendations (Peak Temperature) ^{e, f} | | 260 | | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|------------|---------|---------|------|--|
| Parameter | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^{a, c, d} | R_{thJA} | 40 | 50 | °C/W | |
| Maximum Junction-to-Foot (Drain) | R_{thJF} | 15 | 20 | | |

Notes:

a. Package limited, $T_C = 25$ °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 10$ s.

d. Maximum under Steady State conditions is 95 °C/W.

e. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

f. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

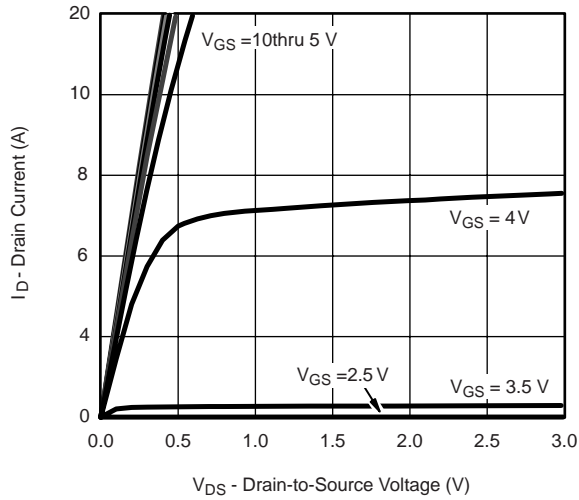
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|--|-------------------------|--|---|-------|-----------|----------------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 60 | | | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | | 25 | | mV/ $^\circ\text{C}$ |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | - 4.0 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 1.0 | | 2.5 | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | 10 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$ | 30 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 4.0\text{ A}$ | | 0.076 | | Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 3.0\text{ A}$ | | 0.085 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 10\text{ V}, I_D = 4.0\text{ A}$ | | 45 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 810 | | pF |
| Output Capacitance | C_{oss} | | | 120 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 100 | | |
| Total Gate Charge | Q_g | $V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 4.0\text{ A}$ | | 22 | 33 | nC |
| | | | $V_{DS} = 30\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 3.0\text{ A}$ | | 10 | |
| Gate-Source Charge | Q_{gs} | | 2.5 | | | |
| Gate-Drain Charge | Q_{gd} | | 1.7 | | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | | 2.4 | | Ω |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD} = 30\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 4.0\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$ | | 15 | 25 | ns |
| Rise Time | t_r | | | 10 | 15 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 35 | 55 | |
| Fall Time | t_f | | | 12 | 20 | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD} = 30\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 4.0\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ | | 10 | 15 | |
| Rise Time | t_r | | | 12 | 20 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 25 | 40 | |
| Fall Time | t_f | | | 10 | 15 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | | | 7.2 | A |
| Pulse Diode Forward Current | I_{SM} | | | | 30 | |
| Body Diode Voltage | V_{SD} | $I_S = 4.0\text{ A}, V_{GS} = 0\text{ V}$ | | 0.8 | 1.2 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 4.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | | 20 | 40 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | 10 | 20 | nC |
| Reverse Recovery Fall Time | t_a | | | 10 | | ns |
| Reverse Recovery Rise Time | t_b | | | 10 | | |

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



V_{DS} - Drain-to-Source Voltage (V)
Output Characteristics



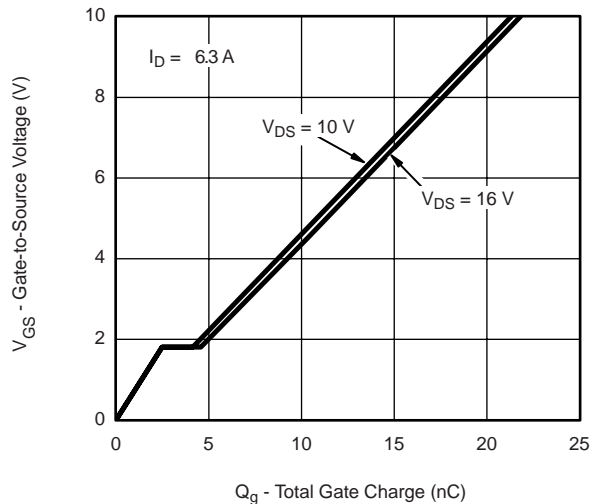
V_{GS} - Gate-to-Source Voltage (V)
Transfer Characteristics



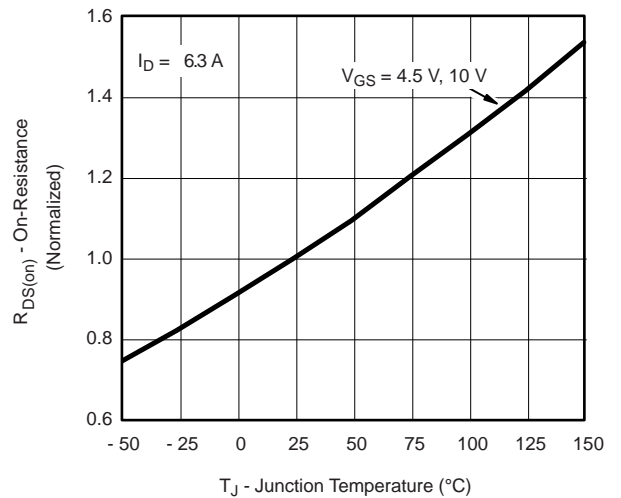
I_D - Drain Current (A)
On-Resistance vs. Drain Current



V_{DS} - Drain-to-Source Voltage (V)
Capacitance

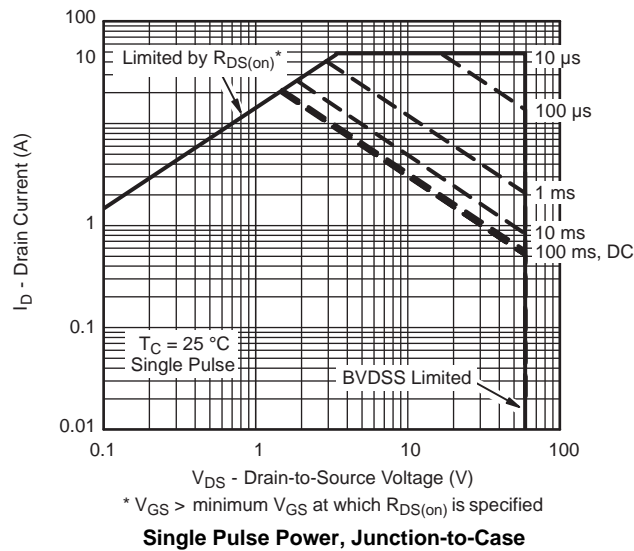
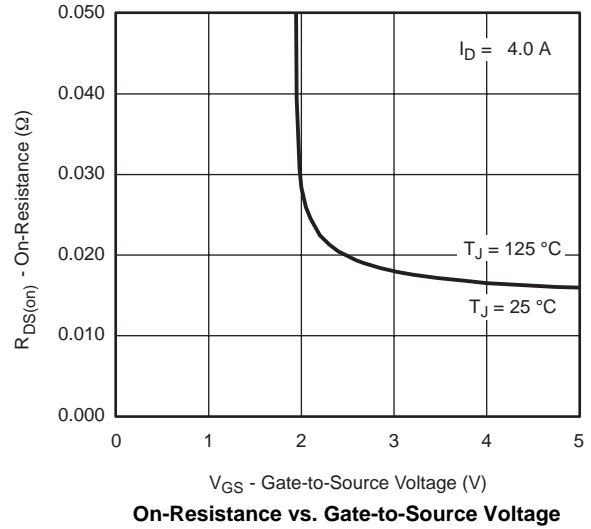


Q_g - Total Gate Charge (nC)
Gate Charge



T_J - Junction Temperature ($^\circ\text{C}$)
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

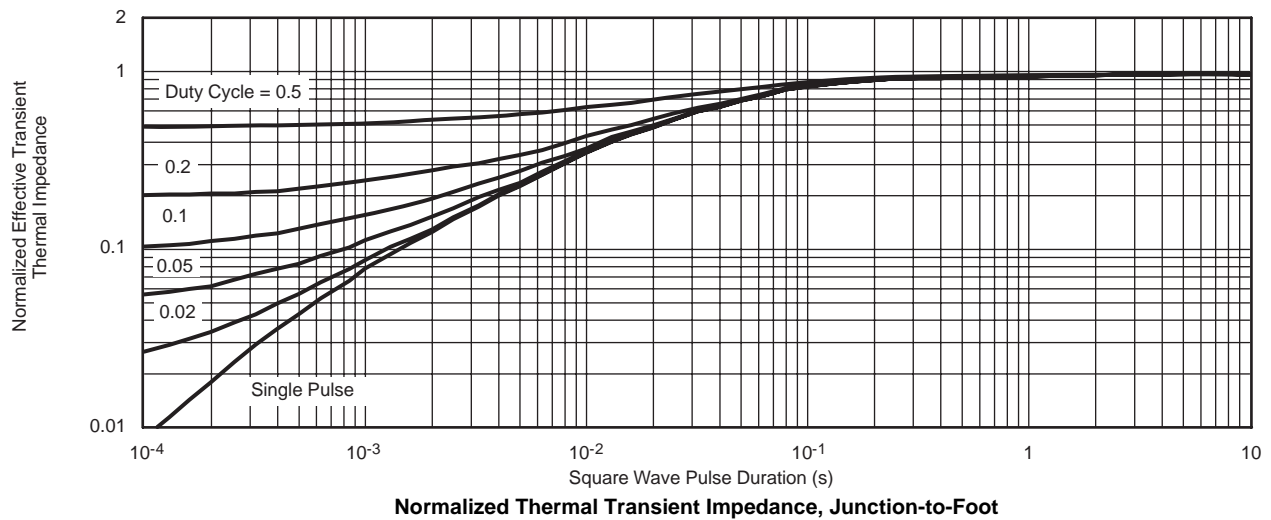
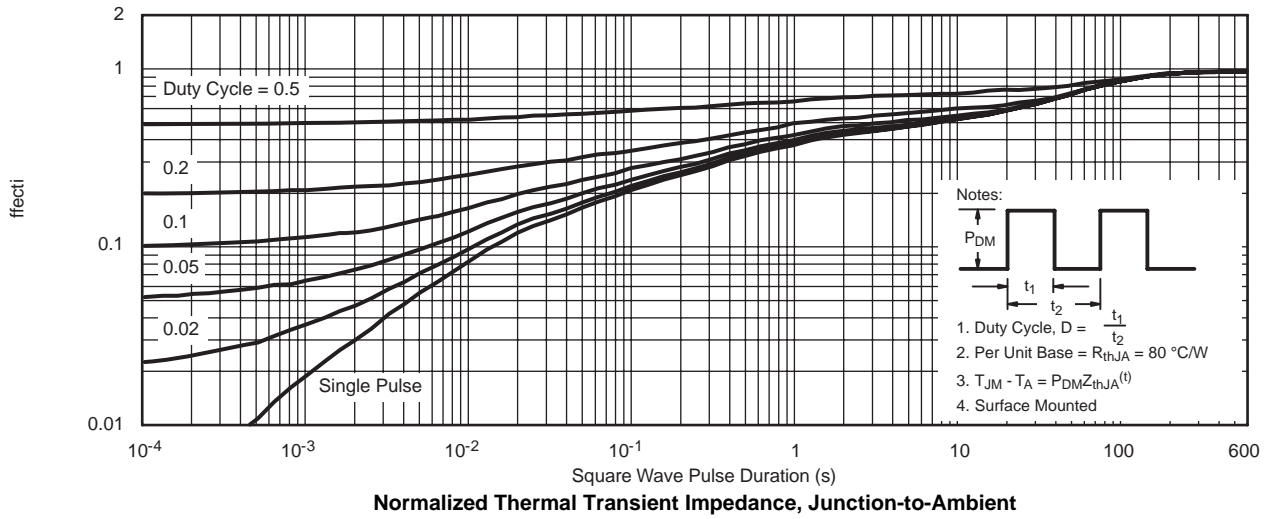


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



SOT-223 (HIGH VOLTAGE)



| DIM. | MILLIMETERS | | INCHES | |
|----------|-------------|------|------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 1.55 | 1.80 | 0.061 | 0.071 |
| B | 0.65 | 0.85 | 0.026 | 0.033 |
| B1 | 2.95 | 3.15 | 0.116 | 0.124 |
| C | 0.25 | 0.35 | 0.010 | 0.014 |
| D | 6.30 | 6.70 | 0.248 | 0.264 |
| E | 3.30 | 3.70 | 0.130 | 0.146 |
| e | 2.30 BSC | | 0.0905 BSC | |
| e1 | 4.60 BSC | | 0.181 BSC | |
| H | 6.71 | 7.29 | 0.264 | 0.287 |
| L | 0.91 | - | 0.036 | - |
| L1 | 0.061 BSC | | 0.0024 BSC | |
| θ | - | 10' | - | 10' |

ECN: S-82109-Rev. A, 15-Sep-08
DWG: 5969

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension do not include mold flash.
4. Outline conforms to JEDEC outline TO-261AA.

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